

PLASMA WASTELESS PROCESSING OF SILICON TETRAFLUORIDE

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SUMMARY

Plasma (H-O-H) chemical process for conversion of silicon tetrafluoride – a voluminous by-product in HF and UF₆ production - to silica and hydrogen fluoride has been studied and demonstrated in the bench-scale plant. The process is tested on a large scale to utilize SiF₄ from the off-gas of a hydrofluoric plant. The SiF₄ - conversion rate reaches 99.5 %, the concentration of resulted HF-acid is in range 42 - 45 %. Silica is produced in the form of γ -tridymite having specific surface area of 200 m²/g and particle mean size of 9 μ .

During the long-time testing in the ARRICT there a few tons of SiF₄ were reprocessed. The experimental results are based upon representative statistic material.

INTRODUCTION

The silicon tetrafluoride (SiF₄) is a by-product of the hydrometallurgical processes where silicate or siliceous ores containing fluorine are subjected to acidic treatment. The process of hydrogen fluoride production by dissolution of fluorospar in sulfuric acid is shown schematically in Figure 1.

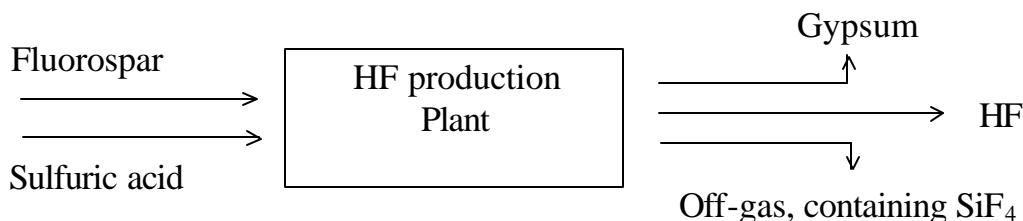


Figure 1. General scheme for production of hydrogen fluoride from fluorospar.

As a result of this process, up to 4 % of fluorine initially containing in fluorospar is lost in the form of SiF₄ polluting the environment of area of hydrofluoric plants. It is very difficult to utilize fluorine from SiF₄ because of its extremely high thermal stability. The problem grows more complicated when SiF₄ is a component of gas mixture containing air and other components.

Off-gas after hydrofluoric plants contains silicon tetrafluoride because of presence of silica in a raw material called fluorospar. As result, there are at least four economical, technical and social problems at these plants:

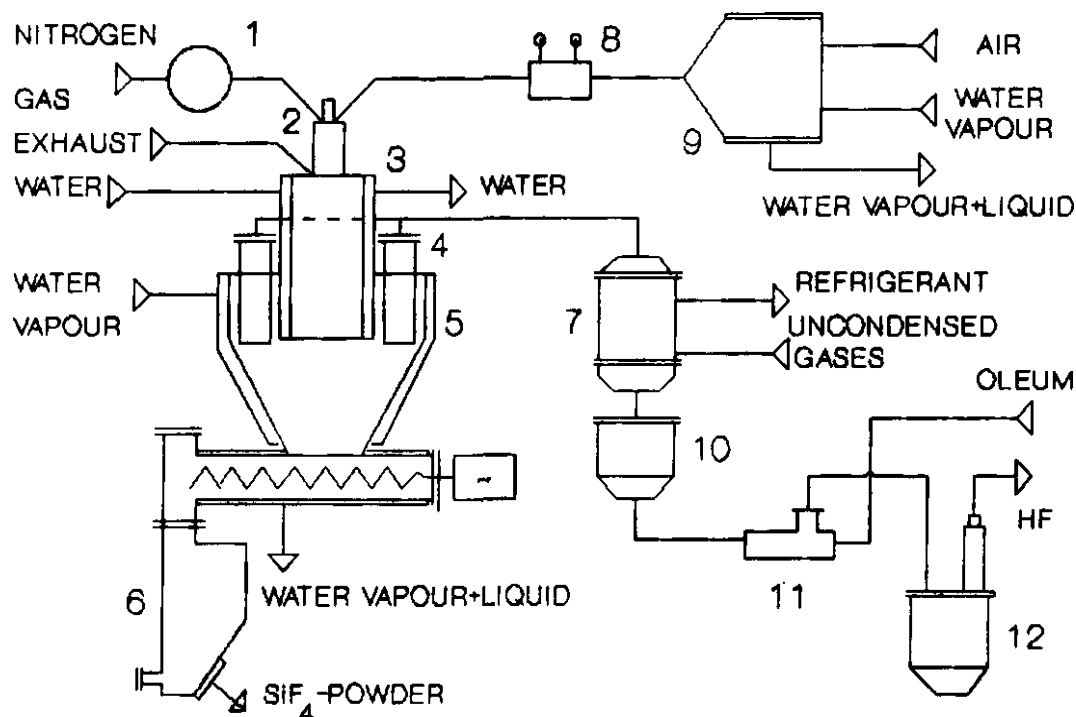


Figure 2. The apparatus scheme of a pilot plant for conversion of silicon tetrafluoride in (H-OH)-plasma: 1-compressor; 2-plasmatron; 3-reactor; 4-filter; 5-intermediate container; 6-container; 7-condenser; 8-steam heater; 9-collector; 10-vessel; 11-mixer; 12-desorber.

A distillation column is not used in this scheme: we produced concentrated hydrofluoric acid was recycled back to the apparatus for producing hydrogen fluoride from fluorospar. Additionally, the apparatus includes a plasma generator and instruments for control and regulation.

Technological parameters of the process are shown in Table 1. Table 2 presents the composition of source and final gas mixtures in large scale experiments. One can see that the initial gas mixture contains 8-18 % SiF_4 . So far as SiF_4 is very diluted one must use large excess of steam. Therefore the hydrofluoric acid obtained is diluted and application of rectification is unprofitable. That is why the scheme of conversion of SiF_4 was simplified: we returned the hydrofluoric acid obtained to the apparatus for producing HF from fluorospar.

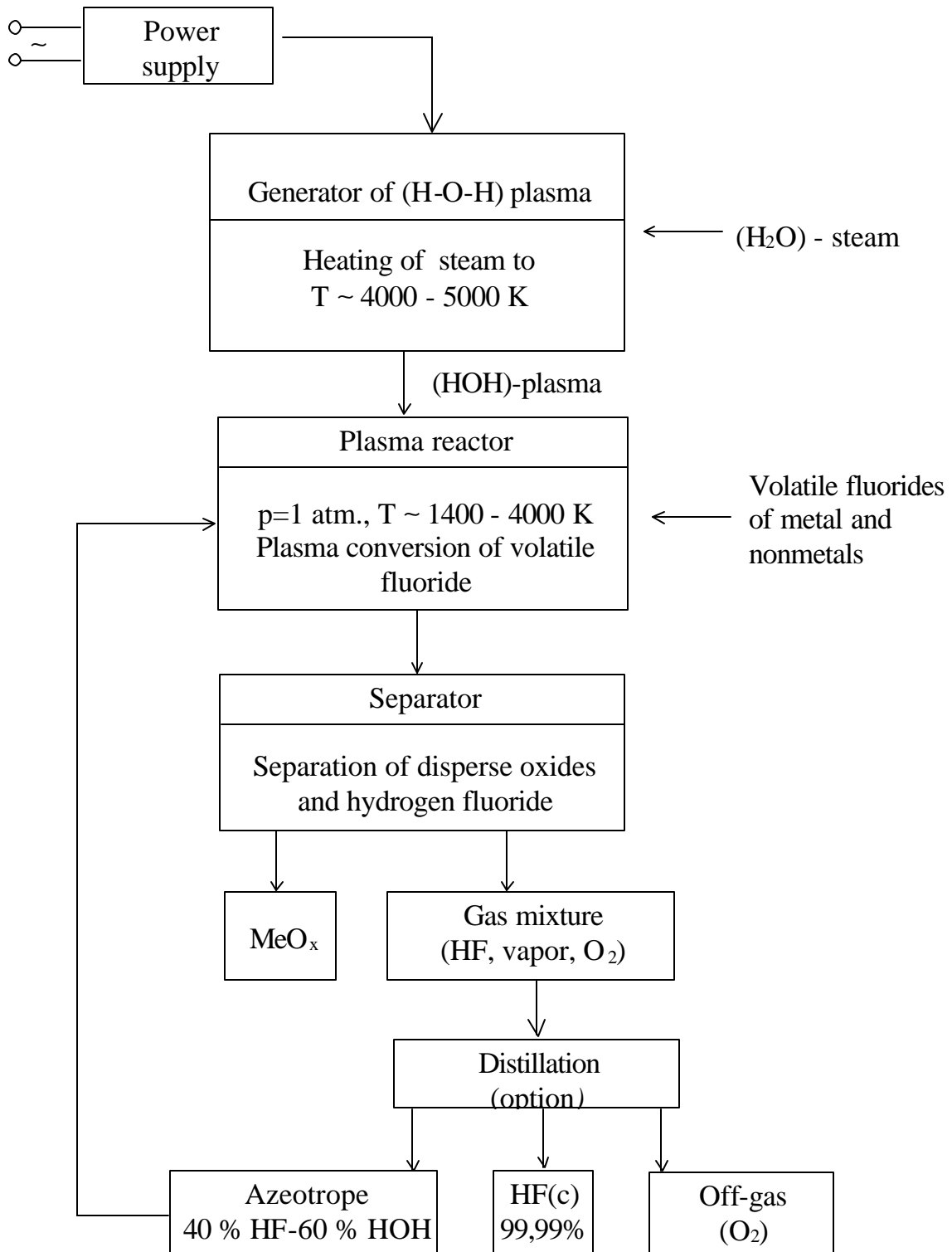


Figure 3. Flow sheet for plasma conversion of volatile fluorides.

Table 1. Parameters of industrial plasma conversion of SiF_4 in off-gas of a hydrofluoric plant

N exp	Plasma Torch Power, kW	Steam supply, kg/h	Gas flow, nm^3/h	$\text{H}_2\text{O}/\text{SiF}_4$ ratio	Mixing Zone temp., K	Full conversion time, s*	SiF_4 conversion rate, %	[HF], % mass.
1	120	30	28	8,0	2600	0.01	99,5	42.2
2	120	30	36	13,0	2100	0,01	94,0	26,3

*) Time of conversion was determined using mathematical modeling (to be published later)

Table 2. Gas composition at the inlet and the outlet of the plasma reactor

N exp.	Gas probe location	Concentration of components, % vol.					
		SiF_4	POF_3	O_2	N_2	HF	Other gases
1	Inlet	18,8	0,2	10,2	54,1	0,0	16,7
	Outlet	0,1	0,0	6,4	67,2	0,0	26,3
2	Inlet	8,2	0,0	6.9	73,4	1,2	10,3
	Outlet	0,5	0,0	7.3	82,0	0,4	9.8

Composition of hydrofluoric acid produced from the off-gas of a hydrofluoric plant is presented in the Table 3. This product was recycled for treatment a fluorospar; as result, the yield of gaseous HF increased by 4 % .

Table 3. Composition of hydrofluoric acid produced by plasma hydrolysis of SiF_4 after hydrofluoric plant

N exp.	Content of the constituents, % mass.				Conversion efficiency ($\text{SiF}_4 \rightarrow \text{HF}$), %
	HF	H_2SiF_6	H_2SO_4	SO_2	
1	40,0	2,40	2,21	0.001	97,8
2	42,14	3.41	1,64	0,001	97,1
3	46,09	2,08	0,98	0,017	98,0

Some properties of second product - silica are presented in Table 4. The product has low bulk density, relatively large specific surface area; one can see that additional thermal treatment of the powder in a discharge from the reactor into a container results in decrease of a specific surface area.

As a rule, the values of specific surface area of SiO₂ powder is in the range from 120 to 212 m²/g. Its bulk density is of 0,05-0,07 g/cm³ without shaking, and of 0,09 g/cm³ after shaking, the size of SiO₂-particles is near 0,08-0,1 μ.

Table 4. Properties of silica produced by plasma conversion of SiF₄ from the off-gas of a hydrofluoric plant

Location of the probe	Bulk density, g/cm ³	SiO ₂ (powder), % mass.	Residual moisture, % mass.	Specific surface area, m ² /g	Residual Fluorine, % mass.
Filter	0,07 - 0,096	93,5	0,19	212	3,1
Container	0,05 - 0,07	89,7	2,17	127	3,5

The silica produced here as a by-product can be used as a filler for rubber articles, as heat and electricity insulator. We studied the physical properties of the product. The values of specific surface area of SiO₂-powder were in the range from 120 to 212 m²/g, its bulk density was of 0,05-0,07g/cm³ without shaking, and of 0,09 g/cm³ after shaking, the size of SiO₂- particles were of 0,08-0,10μ. X-ray analysis of disperse silica produced by SiF₄- plasma conversion reveals metastable form of γ-tridymite.

Heat conductivity of the pressed SiO₂ pellets was determined depending on temperature (Figure 4). It was found that heat conductivity of this material is lower than heat conductivity of the best high temperature heat insulator - natural quartz.

Moreover, it was found that silica obtained is very good insulator in spite of impurities of fluorine and other elements from the raw material used (Figure 5).

The method of a stationary uni-axial thermal flux was used for measurement the heat conductivity and specific resistance of the silica. During the reported here R&D a few metric tons of SiF₄ were treated. So, the presented results are based on a large statistic material on production of hydrofluoric acid and disperse silica.

CONCLUSIONS

From the results of research and development of the plasma process presented we found that at least three technical and social problems can be successfully solved:

- increasing liberation of fluorine from fluorospar up to 99,9 %;
- preventing pollution of environment by gaseous SiF₄;
- producing disperse silica in crystalline or amorphous form.

The conversion rate of SiF_4 increases with increasing the mole ratio $\text{H}_2\text{O}/\text{SiF}_4$ at constant temperature, reaching 99,9 % at $T=3000$ K and $\text{H}_2\text{O}/\text{SiF}_4 \sim 6-8$. However, when the mole ratio $\text{H}_2\text{O}/\text{SiF}_4$ is essentially more than stoichiometric value - 2, concentration of HF-acid is lowered. It was found, that main factor defining high conversion rate of SiF_4 to SiO_2 and HF-acid in combination with high concentration of HF-acid, is the temperature in the plasma reactor. Thus, to produce hydrofluoric acid of mass concentration near 45 %, at conversion step of SiF_4 of 95,7, one must have the temperature in the converter more than 2500 K and the mole ratio $\text{H}_2\text{O}/\text{SiF}_4 = 5$. The by-product of the process is a disperse silica which meets the market requirements as a filler in rubber articles and as a material for heat and electrical insulators.

REFERENCE

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